

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSV)

2SK2995

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

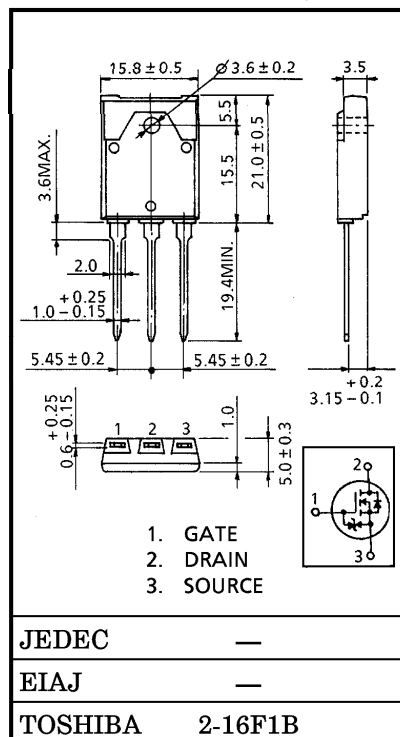
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 48m\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 30S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ ($V_{DS} = 250V$)
- Enhancement-Mode : $V_{th} = 1.5 \sim 3.5V$ ($V_{DS} = 10V$, $I_D = 1mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	250	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	250	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	30
	Pulse	I_{DP}	120
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	90	W
Single Pulse Avalanche Energy**	E_{AS}	925	mJ
Avalanche Current	I_{AR}	30	A
Repetitive Avalanche Energy*	E_{AR}	9	mJ
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$



Weight : 5.8g (Typ.)

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	1.39	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	41.6	$^\circ C/W$

Note ;

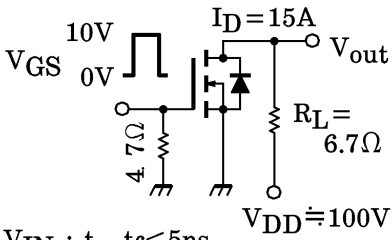
* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 50V$, Starting $T_{ch} = 25^\circ C$, $L = 1.74mH$, $I_{AR} = 30A$, $R_G = 25\Omega$ **This transistor is an electrostatic sensitive device.****Please handle with caution.**

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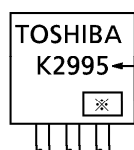
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$	—	—	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 250V, V_{GS} = 0V$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR) DSS}$	$I_D = 10mA, V_{GS} = 0V$	250	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = 15A$	1.5	—	3.5	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 15A$	—	48	0.8	$m\Omega$
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10V, I_D = 15A$	15	30	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10V, V_{GS} = 0V$ $f = 1MHz$	—	5400	—	pF
Reverse Transfer Capacitance		C_{rss}		—	580	—	
Output Capacitance		C_{oss}		—	1900	—	
Switching Time	Rise Time	t_r	 $V_{IN} : t_r, t_f < 5ns,$ $Duty \leq 1\%, t_w = 10\mu s$	—	20	—	ns
	Turn-on Time	t_{on}		—	50	—	
	Fall Time	t_f		—	35	—	
	Turn-off Time	t_{off}		—	200	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq 200V, V_{GS} = 10V$ $I_D = 30A$	—	132	—	nC
Gate-Source Charge		Q_{gs}		—	80	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	52	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	30	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	120	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 30A, V_{GS} = 0V$	—	—	—2.0	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 30A, V_{GS} = 0V$	—	270	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR} / dt = 100A / \mu s$	—	3.0	—	μC

MARKING

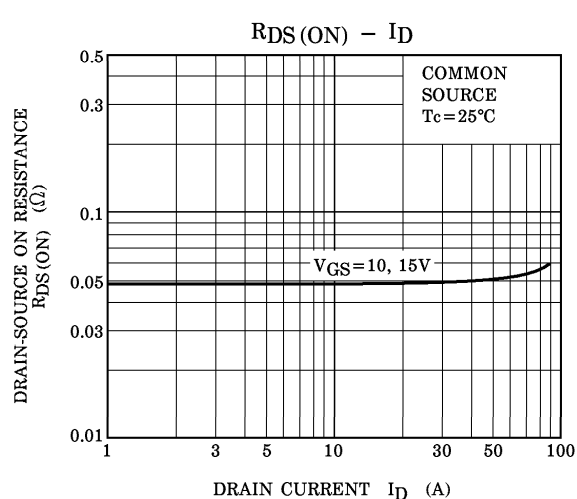
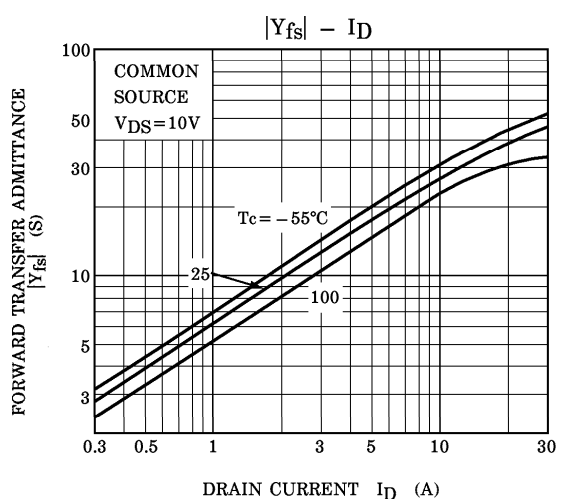
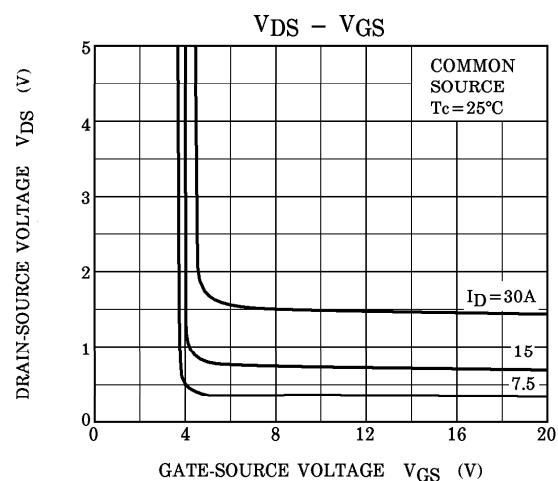
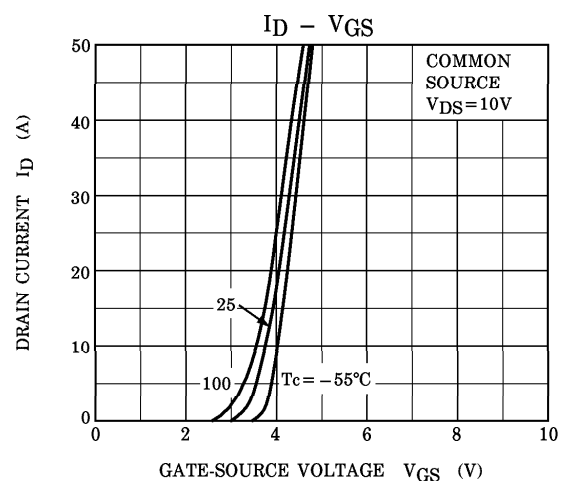
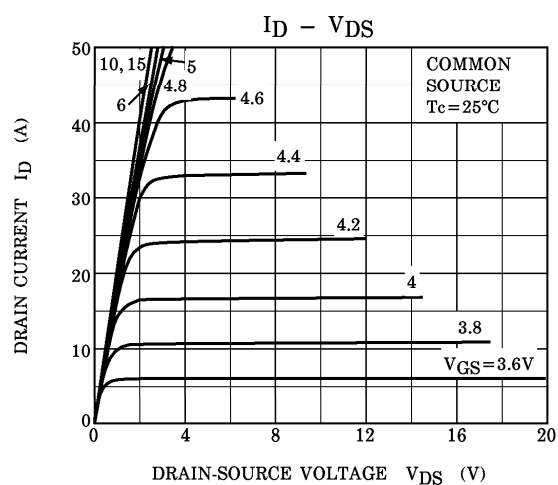
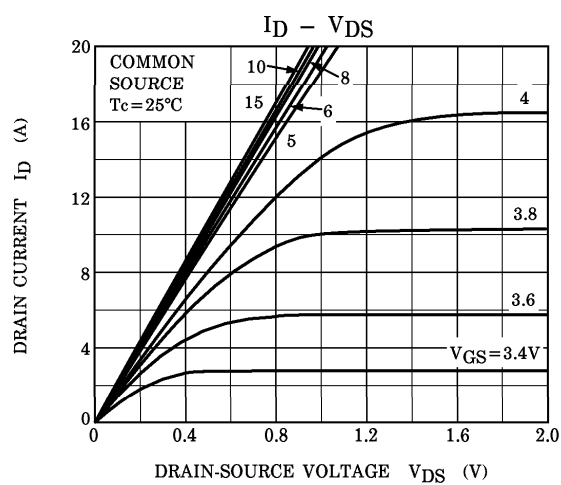


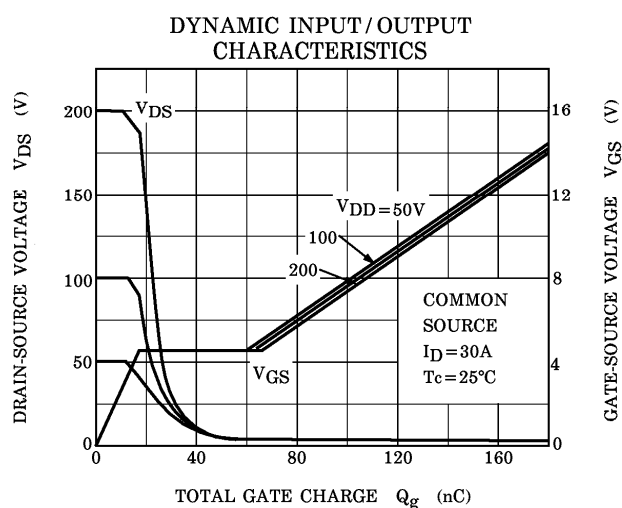
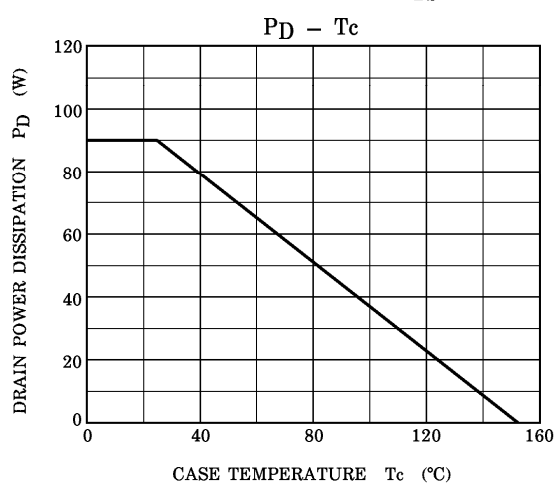
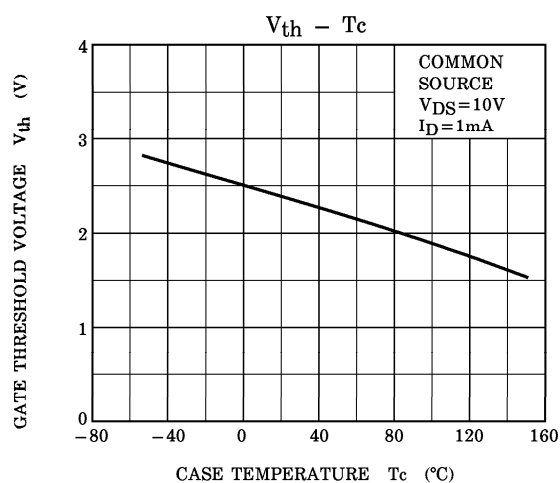
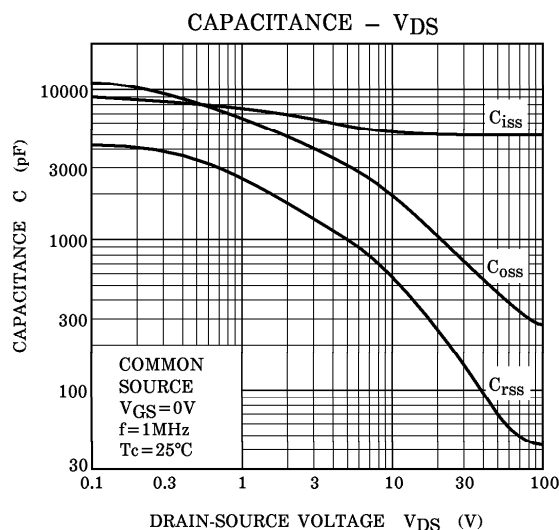
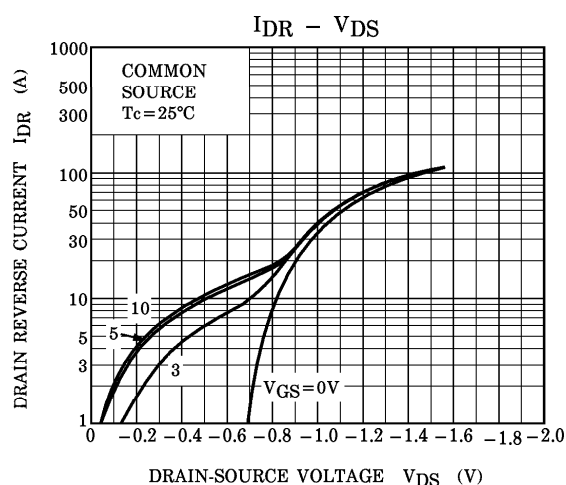
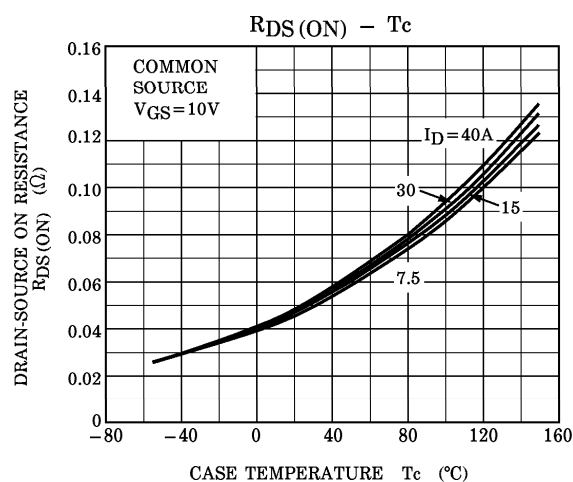
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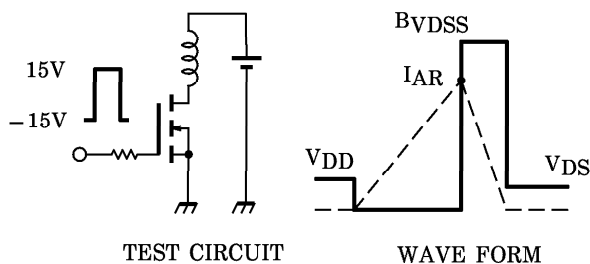
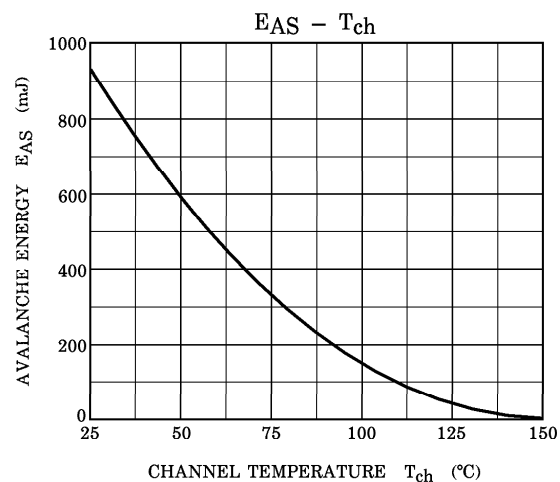
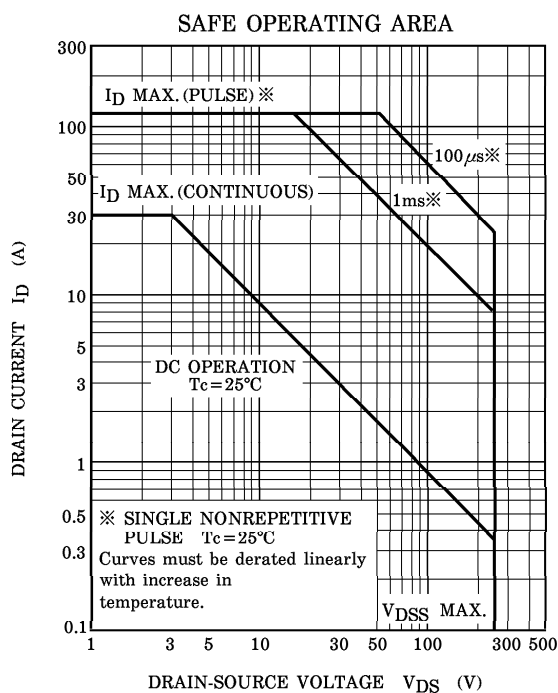
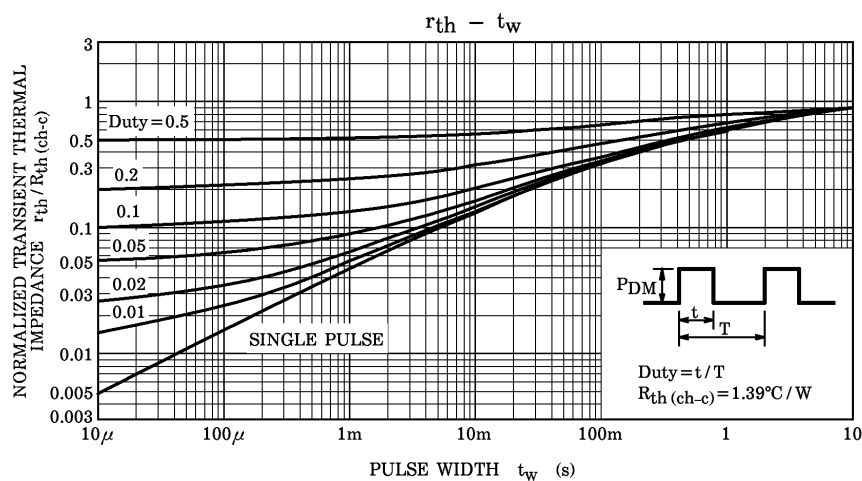
⊗ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = 30\text{A}$, $R_G = 25\Omega$ $V_{DD} = 50\text{V}$, $L = 1.74\text{mH}$

$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$